## **ESD Protection Diode**

# Low Capacitance ESD Protection Diode for High Speed Data Line

The ESD7002 surge protection device is designed to protect high speed data lines from ESD. Ultra-low capacitance and low ESD clamping voltage make this device an ideal solution for protecting voltage sensitive high speed data lines. The flow-through style package allows for easy PCB layout and matched trace lengths necessary to maintain consistent impedance between high speed differential lines such as USB 3.0 and HDMI.

## Features

- Low Capacitance (0.3 pF Typical, I/O to GND)
- Diode capacitance matching
- Protection for the Following IEC Standards:
- IEC 61000-4-2 (Level 4)
- Low ESD Clamping Voltage
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

## **Typical Applications**

- USB2.0/3.0
- LVDS
- HDMI
- High Speed Differential Pairs

## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

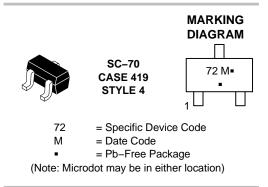
Rating	Symbol	Value	Unit
Operating Junction Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)	ΤL	260	°C
IEC 61000–4–2 Contact (ESD) IEC 61000–4–2 Air (ESD)	ESD ESD	±8 ±15	kV kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

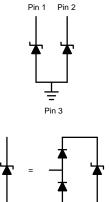


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## PIN CONFIGURATION AND SCHEMATIC



## ORDERING INFORMATION

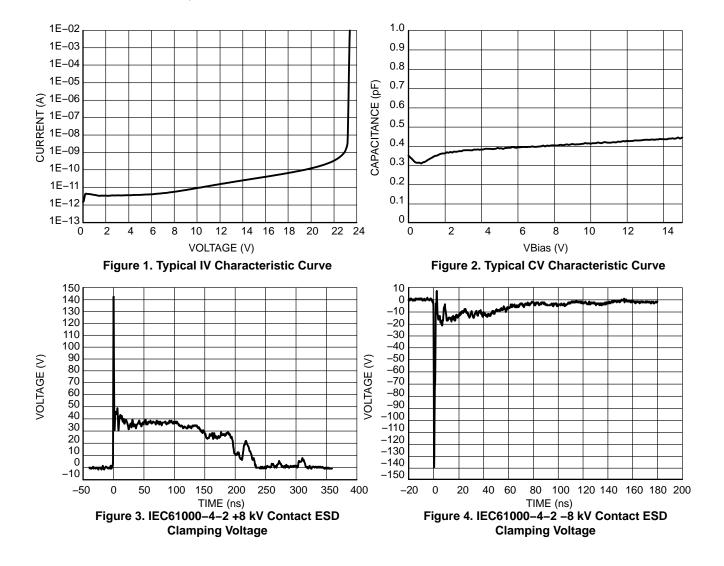
See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V <sub>RWM</sub>	I/O Pin to GND			16	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> = 1 mA, I/O Pin to GND	16.5	23		V
Reverse Leakage Current	Ι <sub>R</sub>	V <sub>RWM</sub> = 5 V, I/O Pin to GND			1	μΑ
Clamping Voltage (Note 1)	V <sub>C</sub>	IEC61000-4-2, ±8 kV Contact	See Figures 3 and 4			
Clamping Voltage TLP (Note 2)	V <sub>C</sub>	I <sub>PP</sub> = 8 A I <sub>PP</sub> = 16 A I <sub>PP</sub> = -8 A I <sub>PP</sub> = -16 A		31.2 33.9 -5.5 -10.8		V
Junction Capacitance Match	$\Delta C_{J}$	VR = 0 V, f = 1 MHz between I/O1 to GND and I/O 2 to GND		5	10	%
Junction Capacitance	CJ	VR = 0 V, f = 1 MHz between I/O Pins		0.2	0.4	pF
Junction Capacitance	CJ	VR = 0 V, f = 1 MHz between I/O Pins and GND 0.3 0.5		0.5	pF	
3dB Bandwidth	f <sub>BW</sub>	R <sub>L</sub> = 50 Ω		5		GHz

1. For test procedure see Figures 5 and 6 and application note AND8307/D.

2. ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions:  $Z_0 = 50 \Omega$ ,  $t_p = 100$  ns,  $t_r = 4$  ns, averaging window;  $t_1 = 30$  ns to  $t_2 = 60$  ns.



## IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

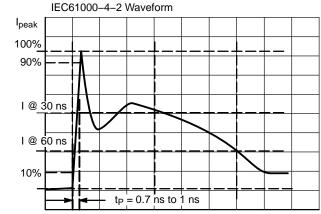


Figure 5. IEC61000-4-2 Spec

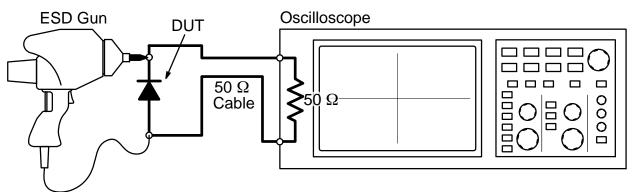


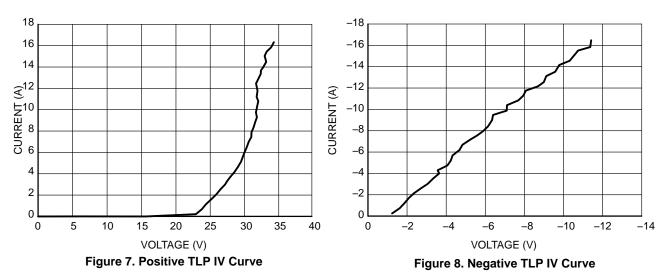
Figure 6. Diagram of ESD Clamping Voltage Test Setup

### The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

## **ESD Voltage Clamping**

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.



NOTE: TLP parameter:  $Z_0 = 50 \Omega$ ,  $t_p = 100$  ns,  $t_r = 300$  ps, averaging window:  $t_1 = 30$  ns to  $t_2 = 60$  ns.

### Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 9. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 10 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.

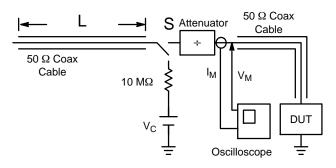


Figure 9. Simplified Schematic of a Typical TLP System

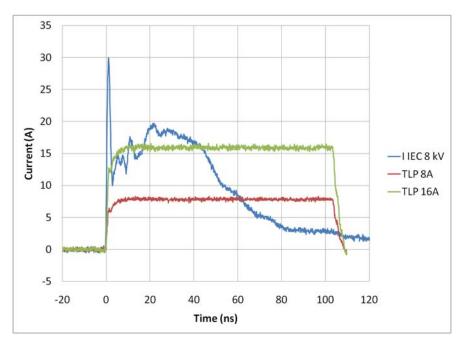


Figure 10. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

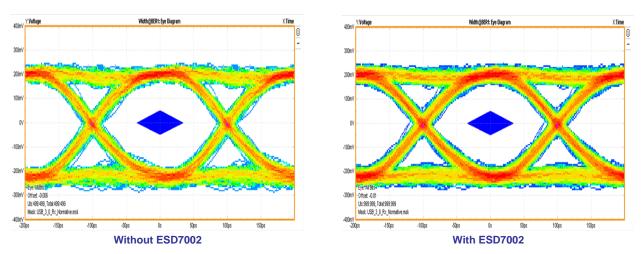
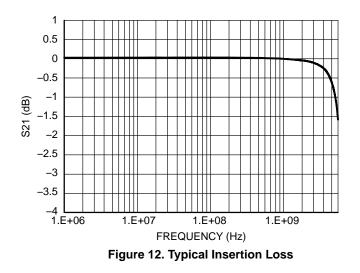


Figure 11. USB3.0 Eye Diagram with and without ESD7002 at 5 Gb/s



## **ORDERING INFORMATION**

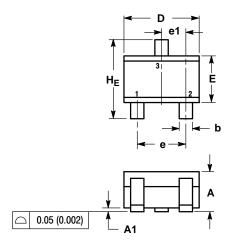
Device	Package	Shipping <sup>†</sup>
ESD7002WTT1G	SC-70 (Pb-Free)	3000 / Tape & Reel
SZESD7002WTT1G*	SC-70 (Pb-Free)	3000 / Tape & Reel

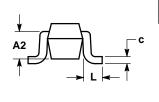
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

## PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 ISSUE N





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

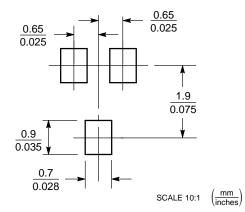
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
Е	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 4: PIN 1. CATHODE

2. CATHODE 3. ANODE

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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